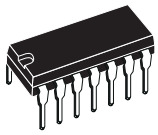
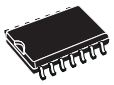
74ACT20

DUAL 4-INPUT NAND GATE

- HIGH SPEED: t_{PD} = 5ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: I_{CC} = 4µA(MAX.) at T_A=25°C
- COMPATIBLE WITH TTL OUTPUTS V_{IH} = 2V (MIN.), V_{IL} = 0.8V (MAX.)
- 50Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL}$ = 24mA (MIN)
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 4.5V to 5.5V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 20
- IMPROVED LATCH-UP IMMUNITY



DIP



SOP



TSSOP

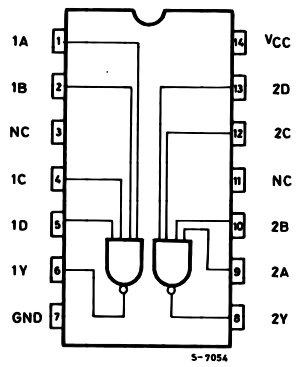
ORDER CODES

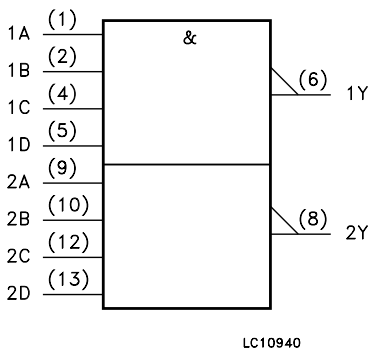
PACKAGE	TUBE	T & R
DIP	74ACT20B	
SOP	74ACT20M	74ACT20MTR
TSSOP		74ACT20TTR

DESCRIPTION

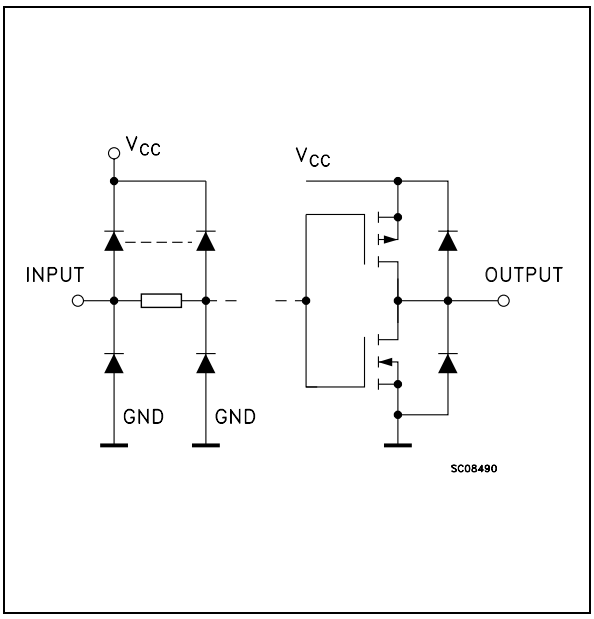
The 74ACT20 is an advanced high-speed CMOS DUAL 4-INPUT NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS tecnology.
The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.
The device is designed to interface directly High Speed CMOS systems with TTL, NMOS and CMOS output voltage levels.
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS





INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 9	1A to 2A	Data Inputs
2, 10	1B to 2B	Data Inputs
3, 11	1C to 2C	Data Inputs
5, 13	1C to 2D	Data Inputs
6, 8	1Y to 2Y	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	C	D	Y
L	X	X	X	H
X	L	X	X	H
X	X	L	X	H
X	X	X	L	H
H	H	H	H	L

X : Don't Care

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter[2]	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 50	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 100	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperqture	-55 to 125	°C
dt/dv	Input Rise and Fall Time V_{CC} = 4.5 to 5.5V (note 1)	8	ns/V

1) V_{IN} from 0.8V to 2.0V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	4.5	V_O = 0.1 V or V_{CC}-0.1V	2.0	1.5		2.0		2.0		V
		5.5		2.0	1.5		2.0		2.0		
V_{IL}	Low Level Input Voltage	4.5	V_O = 0.1 V or V_{CC}-0.1V		1.5	0.8		0.8		0.8	V
		5.5			1.5	0.8		0.8		0.8	
V_{OH}	High Level Output Voltage	4.5	I_O=-50 µA	4.4	4.49		4.4		4.4		V
		5.5	I_O=-50 µA	5.4	5.49		5.4		5.4		
		4.5	I_O=-24 mA	3.86			3.76		3.7		V
		5.5	I_O=-24 mA	4.86			4.76		4.7		
V_{OL}	Low Level Output Voltage	4.5	I_O=50 µA		0.001	0.1		0.1		0.1	V
		5.5	I_O=50 µA		0.001	0.1		0.1		0.1	
		4.5	I_O=24 mA			0.36		0.44		0.5	
		5.5	I_O=24 mA			0.36		0.44		0.5	
I_I	Input Leakage Current	5.5	V_I = V_{CC} or GND			± 0.1		± 1		± 1	µA
I_{CCT}	Max I_{CC}/Input	5.5	V_I = V_{CC} - 2.1V		0.6			1.5		1.6	mA
I_{CC}	Quiescent Supply Current	5.5	V_I = V_{CC} or GND			4		40		80	µA
I_{OLD}	Dynamic Output Current (note 1, 2)	5.5	V_{OLD} = 1.65 V max					75		50	mA
I_{OHD}			V_{OHD} = 3.85 V min					-75		-50	mA

1) Maximum test duration 2ms, one output loaded at time
2) Incident wave switching is guaranteed on transmission lines with impedances as low as 50Ω

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, R_L = 500 Ω, Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	5.0(*)		1.5	5.0	7.2	1.0	9.5	1.0	9.5	ns

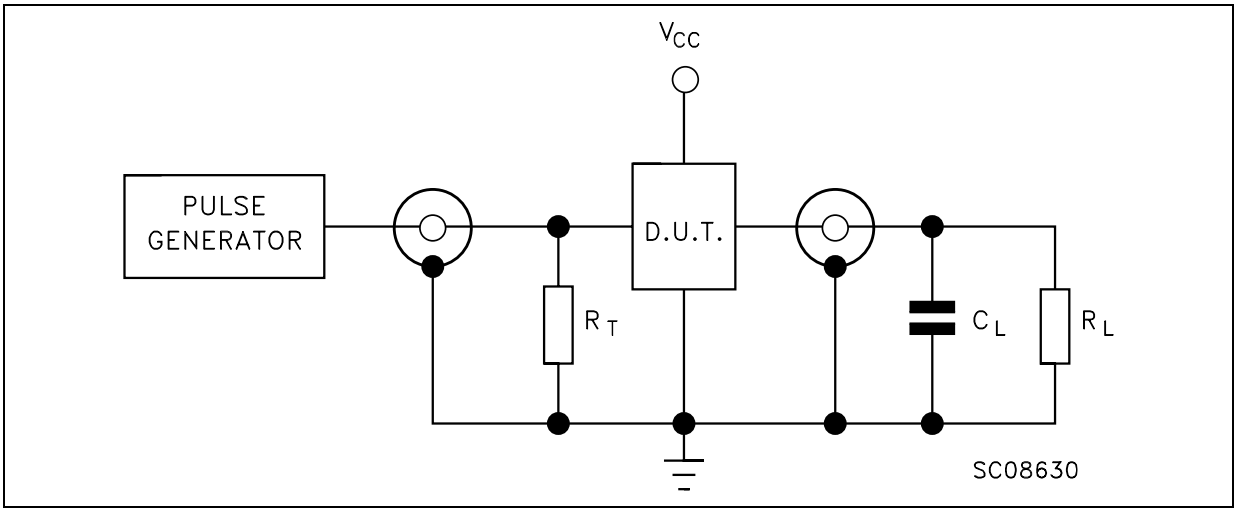
(*) Voltage range is 5.0V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C_{IN}	Input Capacitance	5.0			3.8						pF
C_{PD}	Power Dissipation Capacitance (note 1)	5.0	f_{IN} = 10MHz		33						pF

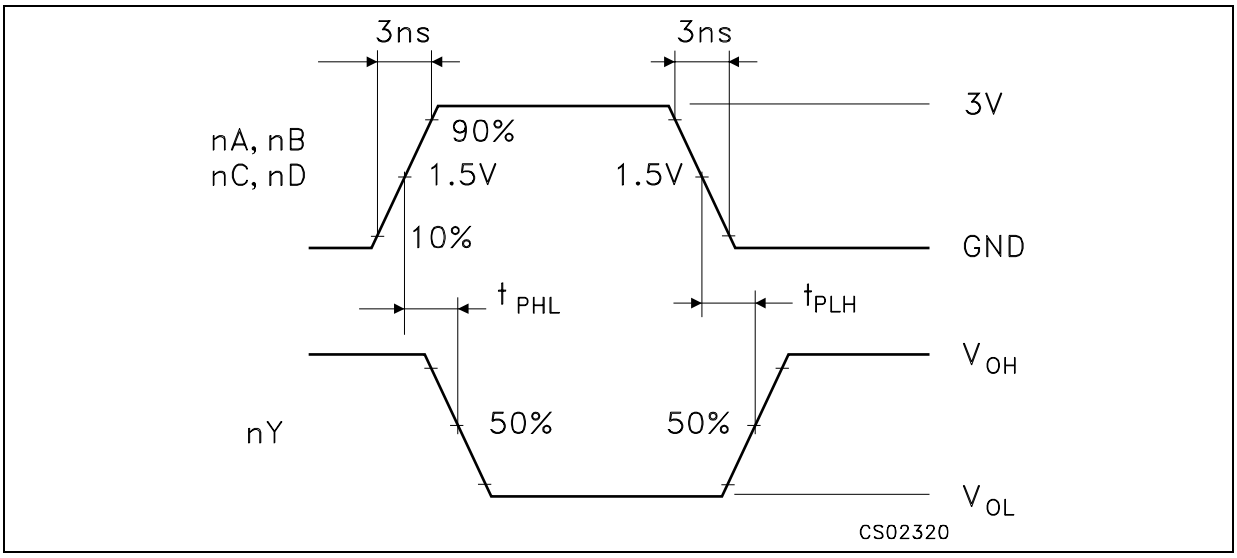
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$ (per gate)

TEST CIRCUIT



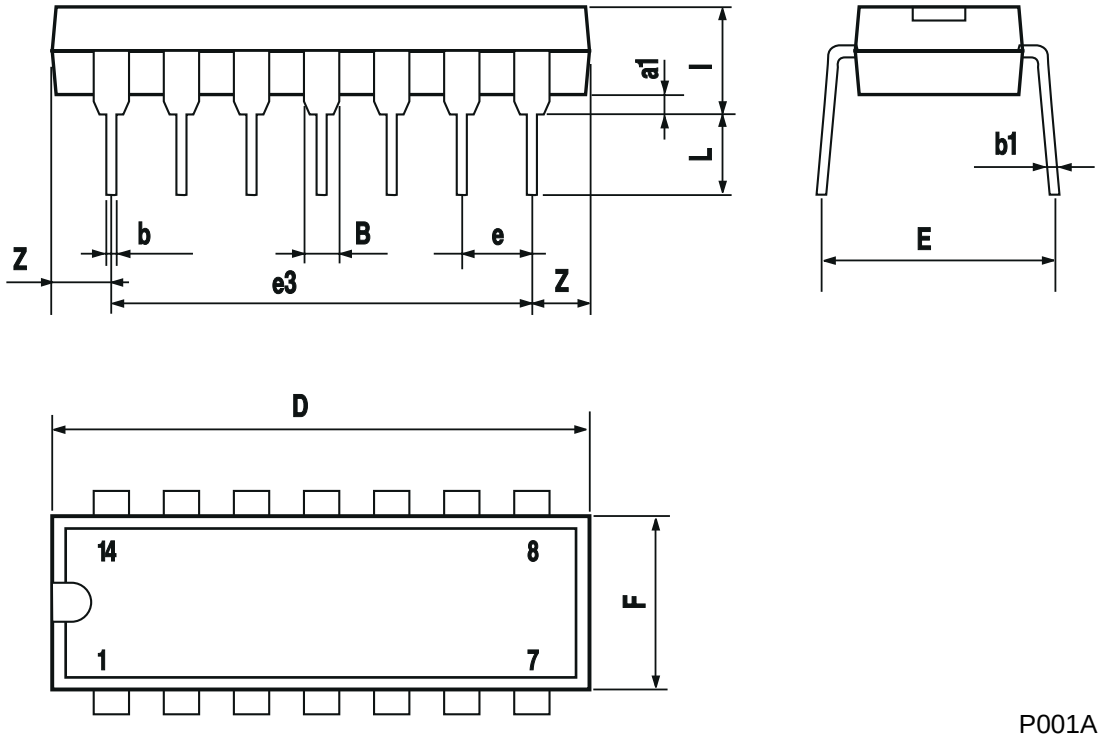
C_L = 50pF or equivalent (includes jig and probe capacitance)
$R_L = R_1$ = 500Ω or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



Plastic DIP-14 MECHANICAL DATA

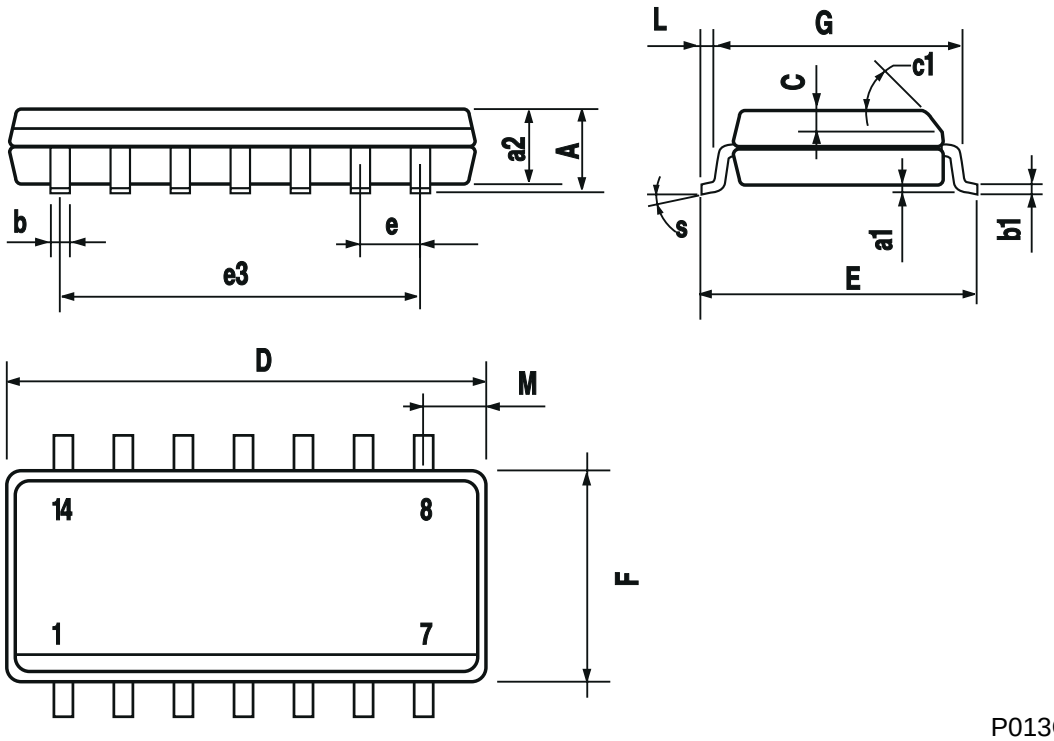
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

SO-14 MECHANICAL DATA

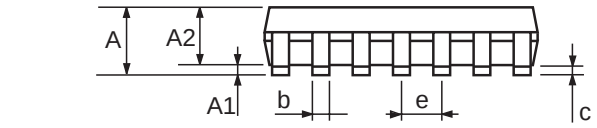
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45 (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8 (max.)					

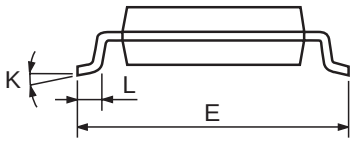


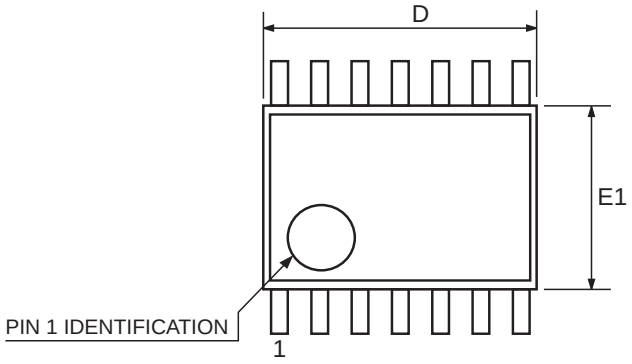
P013G

TSSOP14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.20	0.0035		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0^o	4^o	8^o	0^o	4^o	8^o
L	0.50	0.60	0.70	0.020	0.024	0.028







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